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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/814,570	03/31/2004	Teng-Wang Huang	MAIKP131US	6882
29393	7590 10/30/2006		EXAMINER	
ESCHWEILER & ASSOCIATES, LLC			DEO, DUY VU NGUYEN	
NATIONAL CITY BANK BUILDING 629 EUCLID AVE., SUITE 1000			ART UNIT	PAPER NUMBER
	D, OH 44114	•	1765	
			DATE MAILED: 10/30/2000	6

Please find below and/or attached an Office communication concerning this application or proceeding.

•		Application No.	Applicant(s)				
		10/814,570	HUANG ET AL.				
	Office Action Summary	Examiner	Art Unit				
		Duy-Vu N. Deo	1765				
Period fo	The MAILING DATE of this communication or Reply	appears on the cover sheet	with the correspondence addres	s			
WHIC - Exter after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR RECHEVER IS LONGER, FROM THE MAILING assigns of time may be available under the provisions of 37 CFI SIX (6) MONTHS from the mailing date of this communication period for reply is specified above, the maximum statutory pere to reply within the set or extended period for reply will, by streply received by the Office later than three months after the med patent term adjustment. See 37 CFR 1.704(b).	O DATE OF THIS COMMUN R 1.136(a). In no event, however, may be stried will apply and will expire SIX (6) MO tatute, cause the application to become	IICATION. a reply be timely filed  ONTHS from the mailing date of this communated the communated states of the community s				
Status							
1)⊠	Responsive to communication(s) filed on 2	1 August 2006.					
2a) <u></u> □	This action is <b>FINAL</b> . 2b)⊠ 7	This action is non-final.					
3)	☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
	closed in accordance with the practice und	er <i>Ex parte Quayle</i> , 1935 C	.D. 11, 453 O.G. 213.				
Dispositi	on of Claims						
4)🛛	4) Claim(s) 1-20 is/are pending in the application.						
	4a) Of the above claim(s) is/are withdrawn from consideration.						
5)□	5) Claim(s) is/are allowed.						
6)□							
7)							
8)	Claim(s) are subject to restriction ar	nd/or election requirement.					
Applicati	on Papers						
9)	The specification is objected to by the Exam	niner.		•			
10)	The drawing(s) filed on is/are: a)☐ :	accepted or b)☐ objected to	o by the Examiner.				
	Applicant may not request that any objection to	the drawing(s) be held in abey	ance. See 37 CFR 1.85(a).				
	Replacement drawing sheet(s) including the cor	rrection is required if the drawir	ig(s) is objected to. See 37 CFR 1.	121(d).			
11)	The oath or declaration is objected to by the	Examiner. Note the attach	ed Office Action or form PTO-1	52.			
Priority u	inder 35 U.S.C. § 119						
	Acknowledgment is made of a claim for fore ☐ All b)☐ Some * c)☐ None of:		§ 119(a)-(d) or (f).				
	1. Certified copies of the priority docum						
	2. Certified copies of the priority docum		· ·				
	3. Copies of the certified copies of the p		n received in this National Stag	je			
* 0	application from the International But	, ,,	at received				
3	ee the attached detailed Office action for a	list of the certified copies no	or received.				
Attachmen	t(s)						
	e of References Cited (PTO-892)		Summary (PTO-413)				
	e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO/SB/08)		o(s)/Mail Date  f Informal Patent Application				
	r No(s)/Mail Date	6)  Other: _		•			
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## Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

- (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-20 are rejected under 35 U.S.C. 103(a) as being unpatentable over admitted prior art and in view of Chen et al. (US 6,468,362).

Admitted prior art teaches a wet etching method of a substrate to form deep trench for a DRAM cell comprising: etching the substrate in a first HF tank (claimed vessel); rinsing substrate in second tank; etching the substrate in a third NH4OH tank; rinsing the substrate in a fourth tank; and drying the substrate (pages 1-2 of the specification). Unlike claimed invention, admitted prior art doesn't describe the first rinsing agent comprising at least one wetting agent. Chen describes a method for cleaning the substrate wherein the cleaning solution comprises of a surfactant (claimed rinsing comprising wetting agent) (col. 2, line 65-67; col. 7, line 7-20). It would have been obvious for one skilled in the art to modify admitted prior art in light of Chen by using a cleaning solution with a surfactant because Chen teaches that it would clean the substrate with minimal water marks and residues (col. 1, line 47-57; col. 10, line 31-36). Admitted prior art teaches of successively performing these etching and rinsing steps before the drying step (page 1, line 35-39). Therefore, the combine prior art above would perform the second etching while the wafer is still wet with the rinsing solution with the surfactant.

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Referring to claims 6, 17, Chen describes the wetting agent concentration is 0.01-0.1% by V (claimed 0.01-0.1% by wt).

Referring to claims 7, 9, 18, 19, 20, admitted prior art describes the deep trench has aspect ratio of 50 or more are possible (page 1, line 30-35).

## Claim Rejections - 35 USC § 112

3. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

4. Claims 1-20 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. The specification in page 5, line 5-12, 18-20, doesn't describe or teach performing a second etching step after the first rinsing step while the at least one substrate is wet with the first rinsing agent containing the at least one wetting agent nor while the substrate is wet with the first rinsing agent comprising the at least one wetting agent, arranging the substrate in a third vessel containing a second etchant. It only describes the effect of the wetting agent on the etching step but nothing about how these steps are carried out as claimed. Lines 18-20 describes that the wetting agent forms a part of the etching process, which can be anything including modifying the wafer surface. This still doesn't teach anything about the wafer is wet or

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not wet with rinsing solution with the wetting agent when performing the second etching or moving the wafer into the third vessel containing the second etchant as claimed.

## Response to Arguments

5. Applicant's argument that Chen teaches of rinsing the wafer with water and then drying the wafer is acknowledged. However, in another embodiment he teaches of rinsing with the solution that having surfactant and stopping before the surfactant is completely removed (fig. 1). Therefore, he does suggest keeping the surfactant on the wafer. Furthermore, Chen teaches a series of steps only for a cleaning process including drying the wafer, which would be more likely at the end of the whole process of manufacturing the wafer as described by admitted prior art above. Admitted prior art describes, during a process of manufacturing a wafer, series of steps are carried successively including etching and rinsing before drying the wafer. In this case, the wafer would still have the rinsing solution with the wetting agent when moving to or performing the next etching step.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Duy-Vu N. Deo whose telephone number is 571-272-1462. The examiner can normally be reached on Mon-Fri.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571-272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

> Duy-Vu N Deo **Primary Examiner** Art Unit 1765

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